

## Accepted Manuscript

Title: Photo-detection Characteristics of In-Zn-O/SiO<sub>x</sub>/n-Si Hetero-junctions

Author: Hau-Wei Fang Tsung-Eong Hsieh Jenh-Yih Juang

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- Semiconductor-insulator-semiconductor (SIS) hetero-junction photodetection devices contained indium-zinc-oxide (IZO) layer was fabricated.

- IZO film grown at 250°C possessed a low resistivity and a high optical transmittance in wavelength range from UV to NIR.

- The IZO/SiO<sub>x</sub>/n-Si SIS photodetectors with photoresponse of 35 AW<sup>-1</sup> and 6.15 AW<sup>-1</sup> were separately achieved at visible light and UV light.

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